
2SB1494

Silicon PNP Triple Diffused

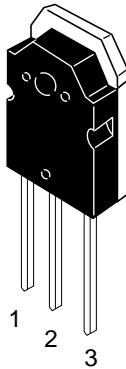
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Application

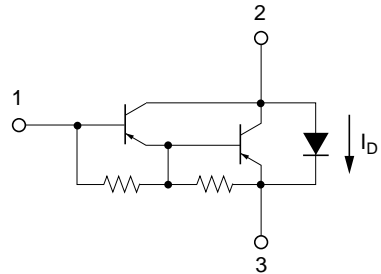
Low frequency power amplifier complementary Pair with 2SD2256

Outline

TO-3P



1. Base
2. Collector
(Flange)
3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

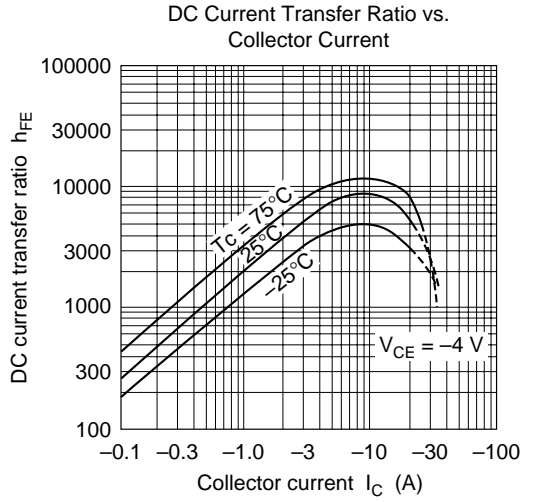
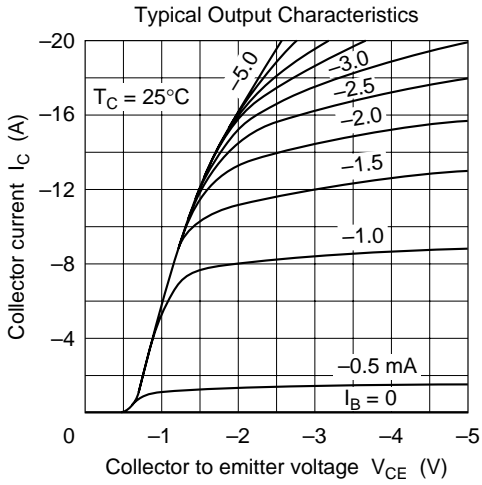
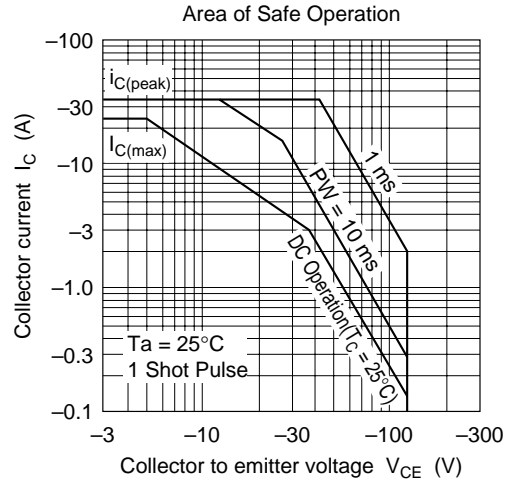
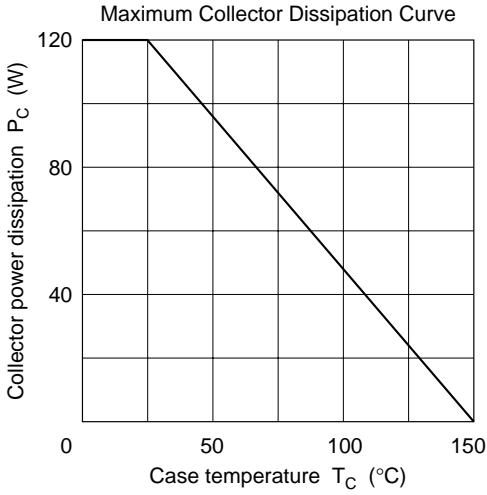
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V_{CEO}	-120	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-25	A
Collector peak current	$I_{C(peak)}$	-35	A
Collector power dissipation	P_C^{*1}	120	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C
C to E diode forward current	I_D^{*1}	25	A

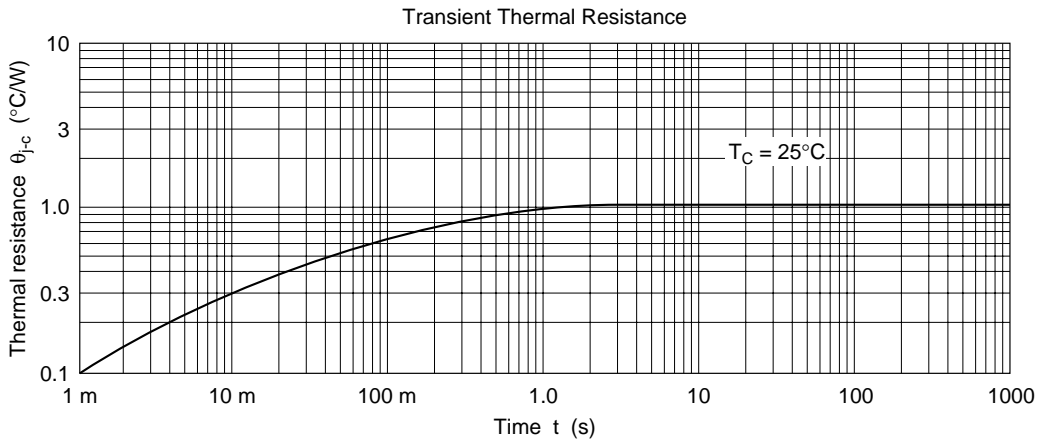
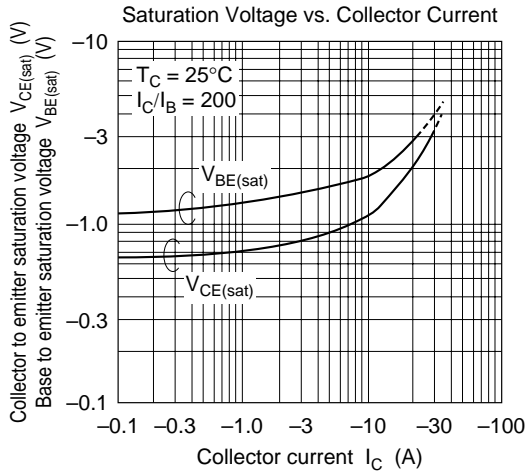
Note: 1. Value at $T_C = 25^\circ\text{C}$.

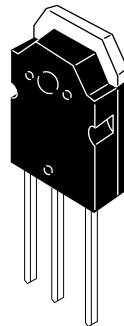
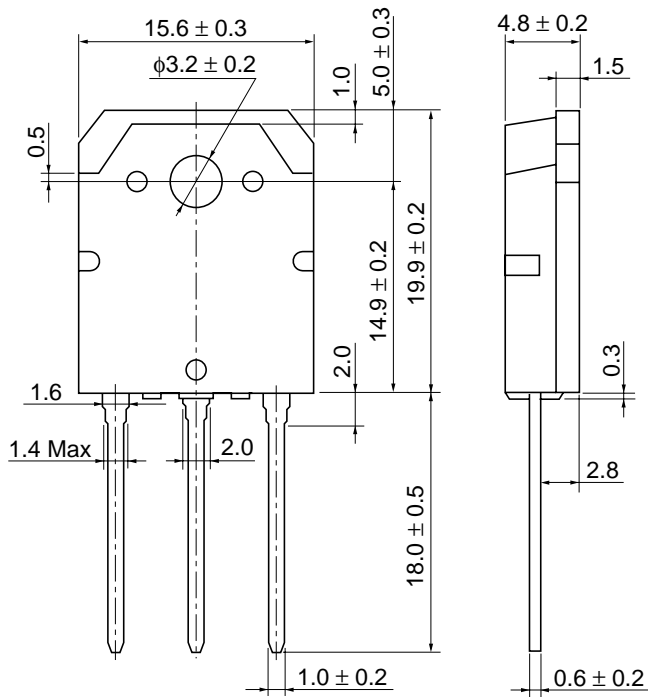
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	—	—	V	$I_C = -0.1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	—	—	V	$I_C = -25 \text{ mA}, R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	-120	—	—	V	$I_C = -200 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-10	μA	$V_{CB} = -100 \text{ V}, I_E = 0$
	I_{CEO}	—	—	-10		$V_{CE} = -100 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h_{FE1}	2000	—	20000		$V_{CE} = -4 \text{ V}, I_C = -12 \text{ A}^{*1}$
	h_{FE2}	500	—	—		$V_{CE} = -4 \text{ V}, I_C = -25 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-2.0	V	$I_C = -12 \text{ A}, I_B = -24 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	-3.5		$I_C = -25 \text{ A}, I_B = -250 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-3.0	V	$I_C = -12 \text{ A}, I_B = -24 \text{ mA}$
	$V_{BE(sat)2}$	—	—	-4.5		$I_C = -25 \text{ A}, I_B = -250 \text{ mA}^{*1}$

Note: 1. Pulse test.







Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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